

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
31 July 2003 (31.07.2003)

PCT

(10) International Publication Number
WO 2003/063169 A3

(51) International Patent Classification⁷: **G11C 11/15**, 11/16

(21) International Application Number:
PCT/US2003/000120

(22) International Filing Date: 2 January 2003 (02.01.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/051,679 16 January 2002 (16.01.2002) US

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(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

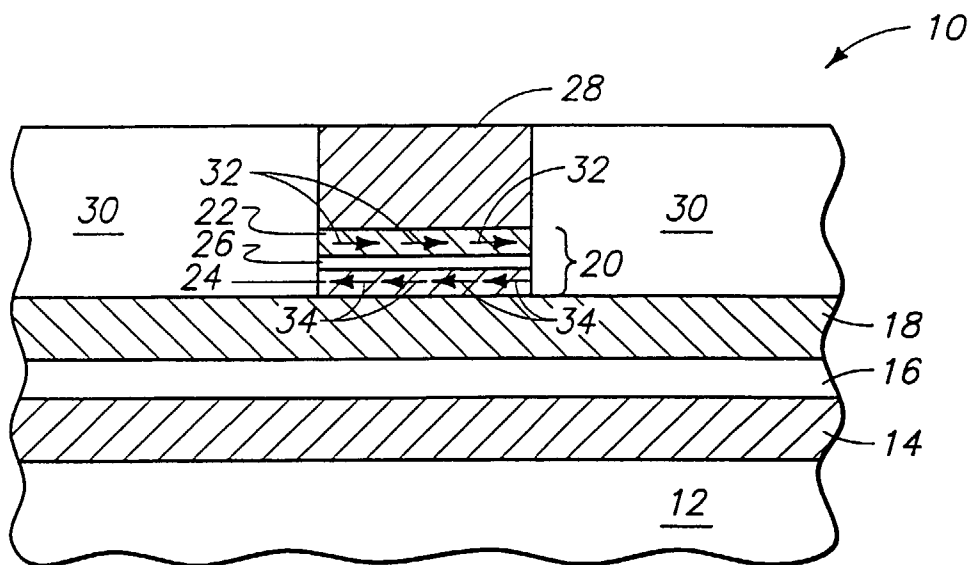
(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— with international search report

(88) Date of publication of the international search report:
31 December 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: **MAGNETORESISTIVE MEMORY DEVICES AND ASSEMBLIES; AND METHODS OF STORING AND RETRIEVING INFORMATION**



(57) **Abstract:** The invention encompasses a magnetoresistive memory device. The device includes a memory bit (20) which comprises a stack having a first magnetic layer (22), a second magnetic layer (24), and a non-magnetic layer (26) between the first and second magnetic layers. A first conductive line (18) is proximate the stack and configured for utilization in reading information from the memory bit. A second conductive line (14) is spaced from the stack by a greater distance than the first conductive line is spaced from the stack, and is configured for utilization in writing information to the memory bit. The invention also encompasses methods of storing and retrieving information in a cross-point array architecture.

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